

PROCESSING METHOD, METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE,
PROCESSING APPARATUS, AND PROGRAM

Abstract

Provided is a technique which provides a substrate including a first surface and a second surface with an inhibitor adsorbed to the first surface and the second surface; and removes a part of the inhibitor adsorbed to the first surface and a part of the inhibitor adsorbed to the second surface by exposing the substrate to a processing agent to reduce or disable a film-formation inhibiting effect by the inhibitor remaining on the second surface while maintaining the film-formation inhibiting effect by the inhibitor remaining on the first surface.

Fig. 4C